

TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SC5548A

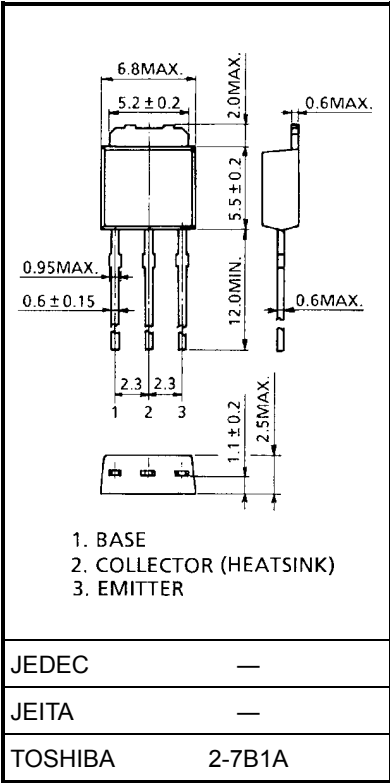
High Voltage Switching Applications
Switching Regulator Applications
DC-DC Converter Applications

- High speed switching: $t_r = 0.5 \mu s$ (max), $t_f = 0.3 \mu s$ (max) ($I_C = 0.8 A$)
- High collector breakdown voltage: $V_{CEO} = 400 V$
- High DC current gain: $h_{FE} = 40$ (min) ($I_C = 0.2 A$)

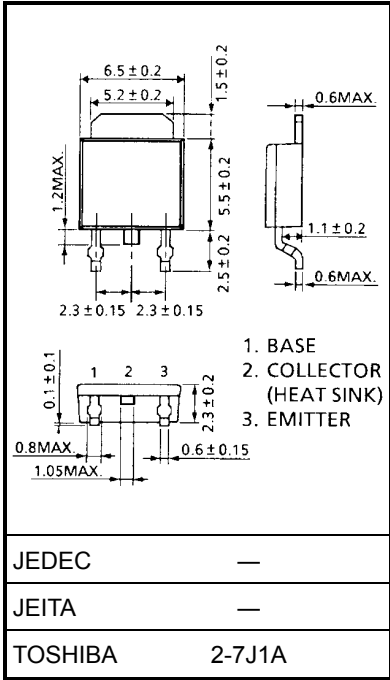
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	600	V
Collector-emitter voltage		V_{CEO}	400	V
Emitter-base voltage		V_{EBO}	7	V
Collector current	DC	I_C	2	A
	Pulse	I_{CP}	4	
Base current		I_B	0.5	A
Collector power dissipation	Ta = 25°C	P_C	1.0	W
	Tc = 25°C		15	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

Unit: mm

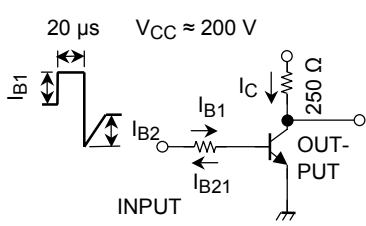


Weight: 0.36 g (typ.)

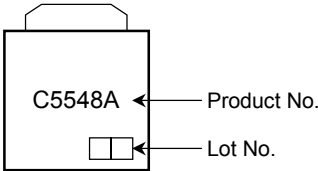


Weight: 0.36 g (typ.)

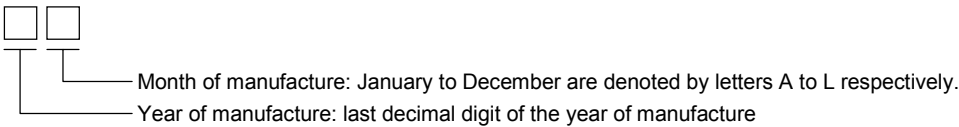
Electrical Characteristics (Ta = 25°C)

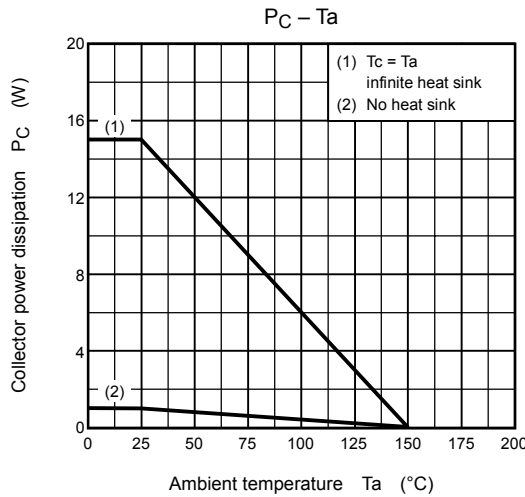
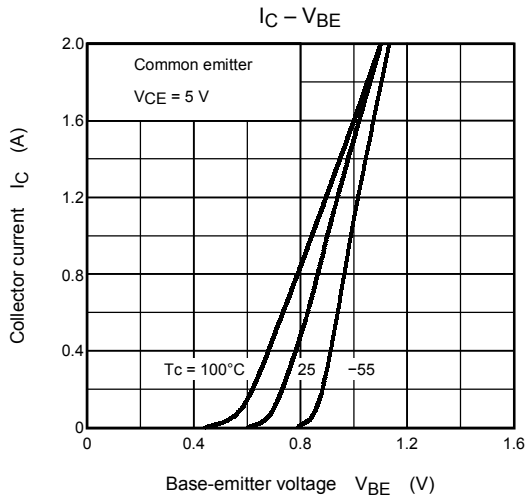
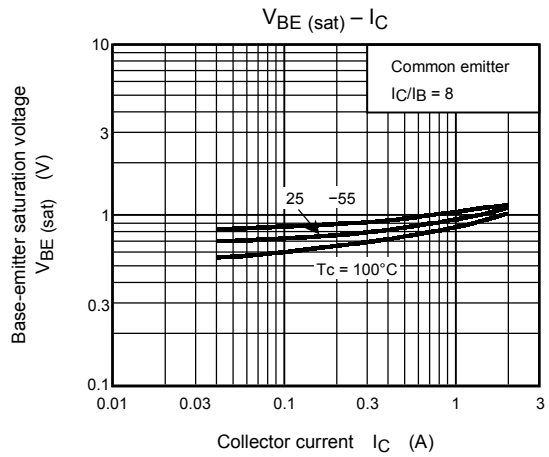
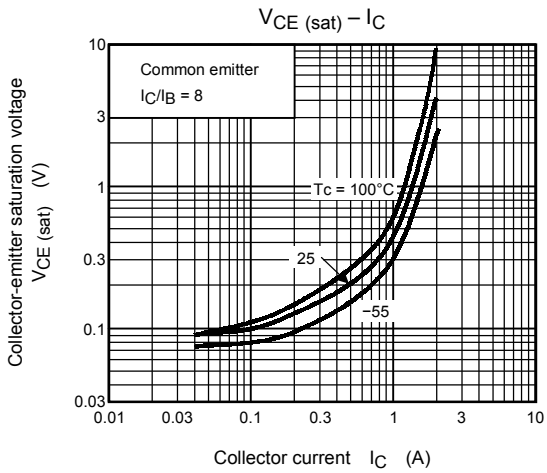
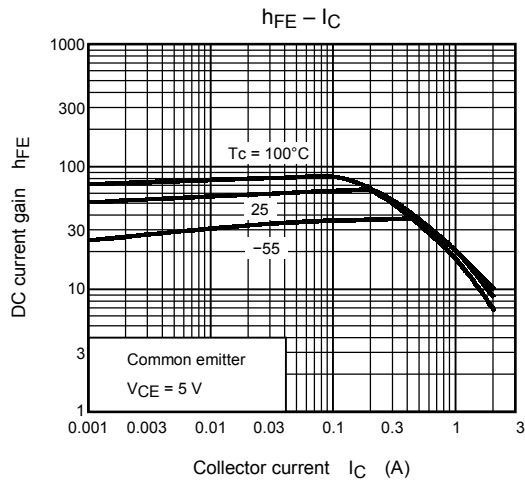
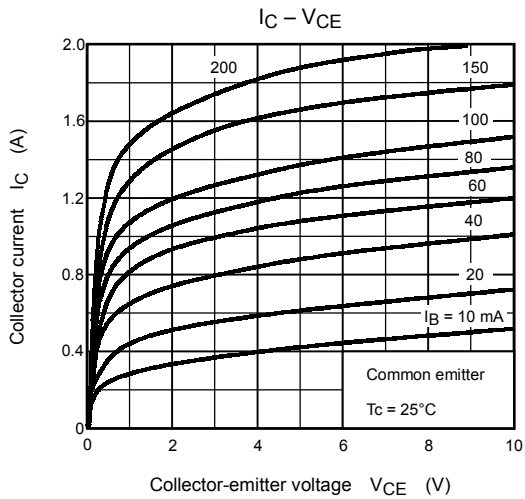
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		ICBO	V _{CB} = 480 V, I _E = 0	—	—	20	μA
Emitter cut-off current		IEBO	V _{EB} = 7 V, I _C = 0	—	—	10	μA
Collector-base breakdown voltage		V _(BR) CBO	I _C = 1 mA, I _E = 0	600	—	—	V
Collector-emitter breakdown voltage		V _(BR) CEO	I _C = 10 mA, I _B = 0	400	—	—	V
DC current gain		h _{FE} (1)	V _{CE} = 5 V, I _C = 1 mA	20	—	—	
		h _{FE} (2)	V _{CE} = 5 V, I _C = 0.2 A	40	—	100	
Collector emitter saturation voltage		V _{CE} (sat)	I _C = 0.8 A, I _B = 0.1 A	—	—	1.0	V
Base-emitter saturation voltage		V _{BE} (sat)	I _C = 0.8 A, I _B = 0.1 A	—	—	1.3	V
Switching time	Rise time	t _r	 I _{B1} = 0.1 A, I _{B2} = -0.2 A DUTY CYCLE ≤ 1%	—	—	0.5	μs
	Storage time	t _{stg}		—	—	3.0	
	Fall time	t _f		—	—	0.3	

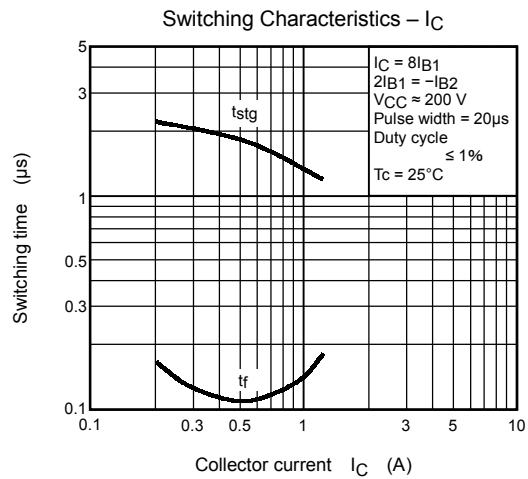
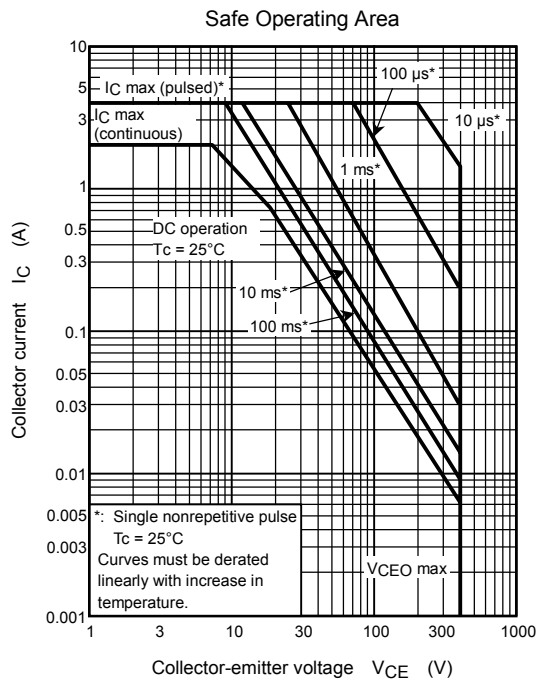
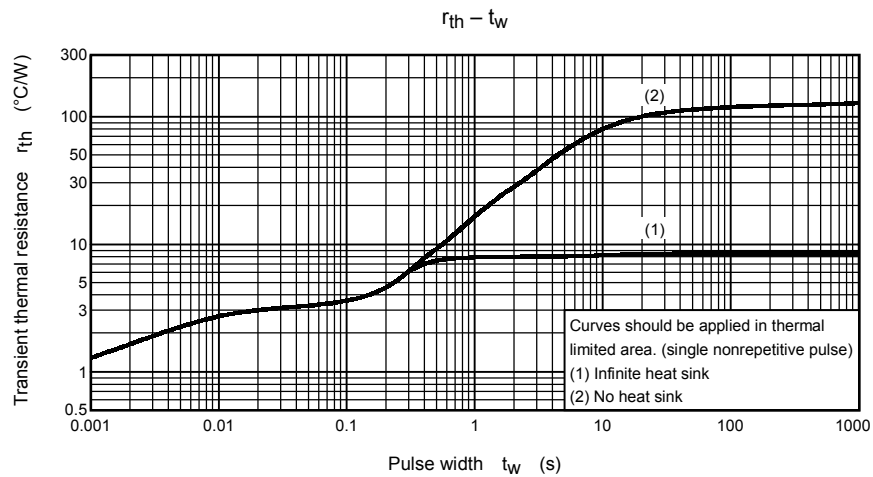
Marking



Explanation of Lot No.







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